

WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:
 a laminated structure of a semiconductor material
 including an active layer formed of a quantum well
 structure;

a low-reflection film formed on one end face of the
 structure;

a high-reflection film formed on the other end face
 of the structure; and

the cavity length of the device being 1,200 μm or
 more.

2. The semiconductor laser device according to claim
 1, wherein said device has a transverse light confinement
 structure with the transverse refractive index difference
 of about 1×10^{-2} for oscillation modes.

3. The semiconductor laser device according to claim
 1, wherein the reflectance of said low-reflection film on
 the one end face is 5% or less.

4. The semiconductor laser device according to claim
 1, wherein said active layer is formed of one or two
 quantum well structures.

5. The semiconductor laser device according to any
 one of claims 1 to 4, wherein the coefficient of light
 confinement to the active layer ranges from 1% to 2%.

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